13 March 2023

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND2	GND (emitter) TR2		O2 I1 GND1
2	12	input (base) TR2		
3	01	output (collector) TR1	<u> </u>	R1 R2
4	GND1	GND (emitter) TR1		TR2
5	I1	input (base) TR1	<u> </u>	R2 R1
6	O2	output (collector) TR2	TSOP6 (SOT457)	GND2 I2 O1
				006aab235

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
PIMD2	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PIMD2	M5

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

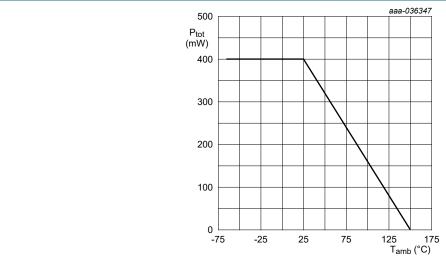
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or		,			
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V _{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V _{EBO}	emitter-base voltage	open collector	[1]	-	10	V
V _I	input voltage	TR1 (NPN)		-10	40	V
		TR2 (PNP)		-40	10	V
Io	output current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	250	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	400	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	313	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

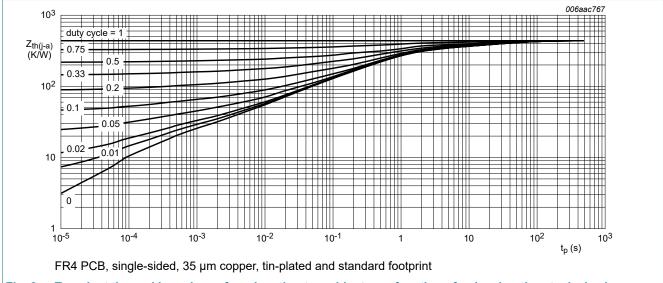


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

10. Characteristics

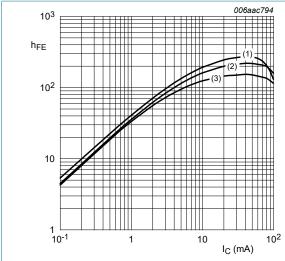
Table 7. Characteristics

r						
collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
collector-base cut-off current	$I_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	[1]	-	-	5	μΑ
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	180	μΑ
DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	60	-	-	
collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	[1]	-	-	150	mV
off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	1.1	0.8	V
on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		2.5	1.7	-	V
bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
bias resistor ratio		[2]	0.8	1	1.2	
'						
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[3]	-	230	-	MHz
			•			
collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	-	3	pF
transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[3]	-	180	-	MHz
	collector-emitter breakdown voltage collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage off-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance transition frequency	collector-emitter breakdown voltage	collector-emitter breakdown voltage $I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ [1] collector-base cut-off current $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ [1] collector-emitter cut-off current $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ [1] emitter-base cut-off current $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$ [1] emitter-base cut-off current $V_{CE} = 5 \text{ V}; I_C = 0 \text{ mA}; T_{amb} = 25 \text{ °C}$ [1] collector-emitter $V_{CE} = 5 \text{ V}; I_C = 5 \text{ mA}; T_{amb} = 25 \text{ °C}$ [1] collector-emitter saturation voltage $V_{CE} = 5 \text{ V}; I_C = 100 \text{ µA}; T_{amb} = 25 \text{ °C}$ [1] on-state input voltage $V_{CE} = 5 \text{ V}; I_C = 100 \text{ µA}; T_{amb} = 25 \text{ °C}$ [1] collector capacitance $V_{CE} = 0.3 \text{ V}; I_C = 5 \text{ mA}; T_{amb} = 25 \text{ °C}$ [2] bias resistor 1 (input) [2] collector capacitance $V_{CE} = 10 \text{ V}; I_C = 10 \text{ mA}; I_C$	$ \begin{array}{c} \text{collector-emitter} \\ \text{breakdown voltage} \\ \\ \text{collector-base cut-off} \\ \text{current} \\ \\ \text{collector-base cut-off} \\ \text{current} \\ \\ \text{collector-emitter cut-off} \\ \text{current} \\ \\ \text{collector-base cut-off} \\ \text{current} \\ \\ \text{current} \\ \\ \text{collector-emitter} \\ \text{current} \\ \\ \text{collector-emitter} \\ \text{saturation voltage} \\ \text{off-state input voltage} \\ \text{off-state input voltage} \\ \text{off-state input voltage} \\ \text{v}_{\text{CE}} = 5 \text{ V; I}_{\text{C}} = 5 \text{ mA; T}_{\text{amb}} = 25 \text{ °C} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = 0.3 \text{ V; I}_{\text{E}} = 0.5 \text{ mA; T}_{\text{amb}} = 25 \text{ °C} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = 0.3 \text{ V; I}_{\text{C}} = 5 \text{ mA; T}_{\text{amb}} = 25 \text{ °C} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = 0.3 \text{ V; I}_{\text{E}} = 0 \text{ A; i}_{\text{e}} = 0 \text{ A; f} = 1 \text{ MHz; T}_{\text{amb}} = 25 \text{ °C} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = 5 \text{ V; I}_{\text{C}} = 100 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = 5 \text{ V; I}_{\text{C}} = 10 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -10 \text{ V; I}_{\text{E}} = 0 \text{ A; i}_{\text{e}} = 0 \text{ A; f} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -10 \text{ V; I}_{\text{E}} = 0 \text{ A; i}_{\text{e}} = 0 \text{ A; f} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -5 \text{ V; I}_{\text{C}} = -10 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -5 \text{ V; I}_{\text{C}} = -10 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -5 \text{ V; I}_{\text{C}} = -10 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -5 \text{ V; I}_{\text{C}} = -10 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{collector capacitance} \\ \text{v}_{\text{CE}} = -5 \text{ V; I}_{\text{C}} = -10 \text{ mA; f} = 100 \text{ MHz; } \\ \text{collector capacitance} \\ \text{collector capacitance} \\ \text{collector capacitance} \\ \text{collector capacitance} \\ collector capacitance$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] For the PNP transistor with negative polarity.

^[2] See section "Test information" for resistor calculation and test conditions.

^[3] Characteristics of built-in transistor

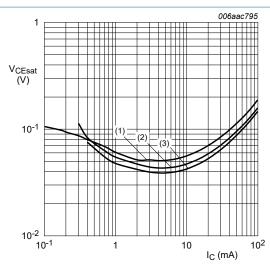


$$V_{CE} = 5 V$$

$$(1) T_{amb} = 100 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



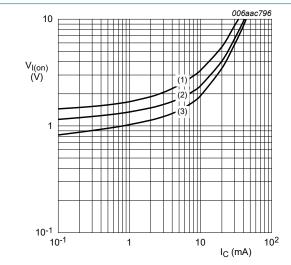
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = 100 \, ^{\circ}C$
(2) $T_{amb} = 25 \, ^{\circ}C$
(3) $T_{amb} = -40 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



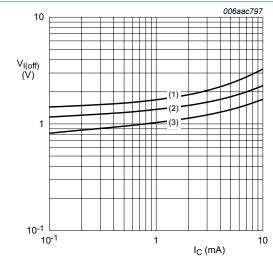
$$V_{CE}$$
 = 0.3 V

$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

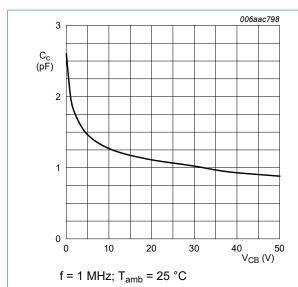
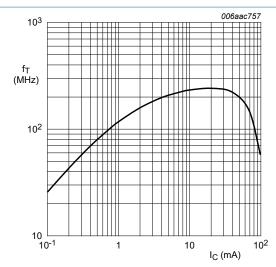
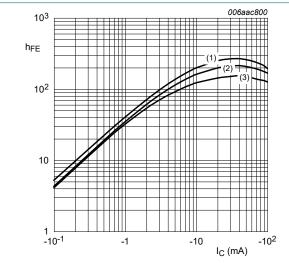


Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



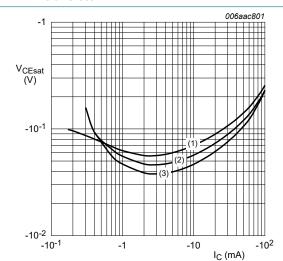
f = 100 MHz $T_{amb} = 25 \text{ °C}$ $V_{CE} = 5 \text{ V}$

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



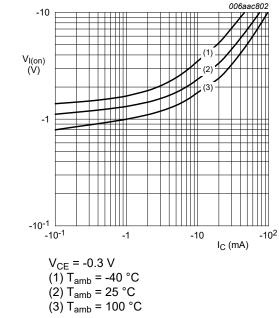
 V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values

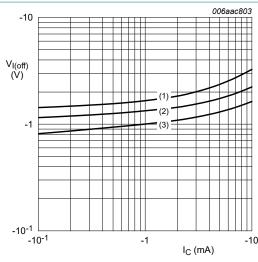


 $I_C/I_B = 20$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -40 \,^{\circ}C$

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



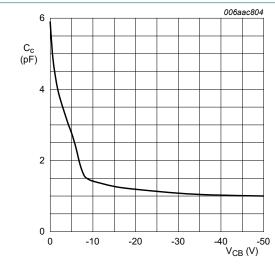
of collector current; typical values



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C

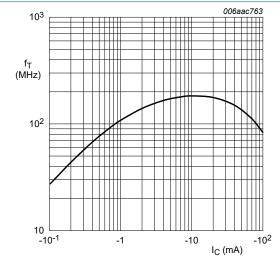
(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $f = 1 MHz; T_{amb} = 25 °C$

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 T_{amb} = 25 °C

 $V_{CE} = -5 V$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

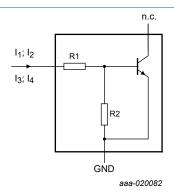


Fig. 15. TR1 (NPN): Resistor test circuit

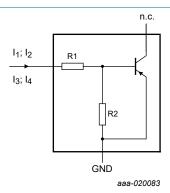


Fig. 16. TR2 (PNP): Resistor test circuit

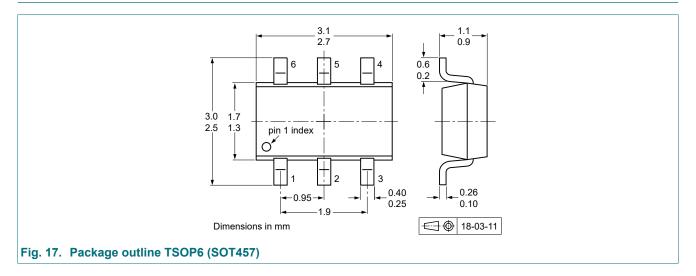
Resistor test conditions

Table 8. Resistor test conditions

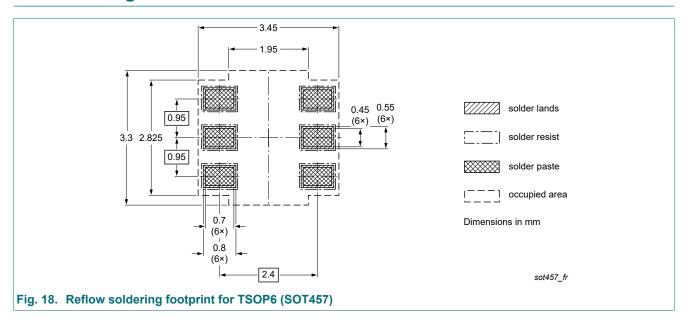
PIMD2	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	l ₂	l ₃	14
TR1 (NPN)	22	22	150 μΑ	230 μΑ	-150 μA	-230 μA
TR2 (PNP)	22	22	-150 μA	-230 μA	150 μΑ	230 μΑ

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

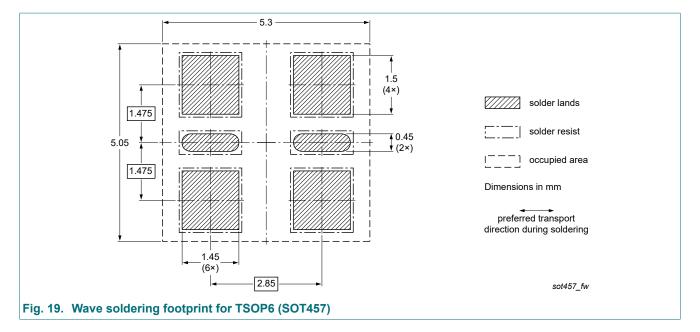
12. Package outline



13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

14. Revision history

Table 9. Revision history

Table 5. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PIMD2 v.9	20230313	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.8	
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet splitted to single type data sheets. 				
PEMD2_PIMD2_PUMD2 v.8	20131114	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.7	
PEMD2_PIMD2_PUMD2 v.7	20080924	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.6	
PEMD2_PIMD2_PUMD2 v.6	20042104	Product specification	-	PEMD2_PIMD2_PUMD2 v.5	
PEMD2_PIMD2_PUMD2 v.5	20030606	Product specification	-	-	

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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PIMD2

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50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

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